

TGD N-Channel Enhancement Mode Power MOSFET

Description

The TGD15H10A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

General Features

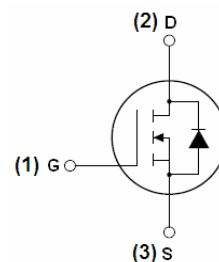
- $V_{DS} = 150V, I_D = 100A$
 $R_{DS(ON)} < 11m\Omega @ V_{GS} = 10V$ (Typ: 9.5m Ω)
- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

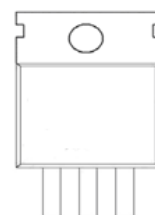
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

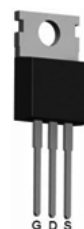
100% ΔV_{ds} TESTED!



Schematic diagram



pin assignment



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
15H10A	15H10A	TO-220-3L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	100	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	70	A
Pulsed Drain Current	I_{DM}	390	A
Maximum Power Dissipation	P_D	370	W
Derating factor		2.47	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	1600	mJ



Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C
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Thermal Characteristic

Thermal Resistance, Junction-to-Cas ^e (Note 2)	$R_{\theta JC}$	0.41	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

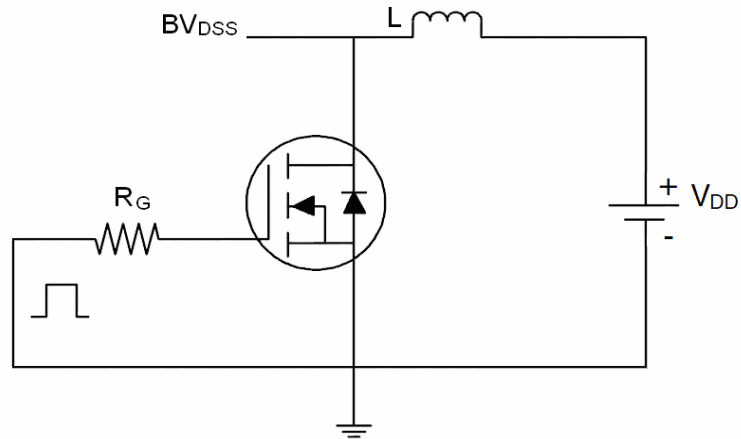
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	150	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.7	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$	-	9.5	11	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=40A$	100	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$	-	7500	-	PF
Output Capacitance	C_{oss}		-	640	-	PF
Reverse Transfer Capacitance	C_{rss}		-	426	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=75V, I_D=2A, R_L=15\Omega$ $, R_G=2.5\Omega, V_{GS}=10V$	-	32.5	-	nS
Turn-on Rise Time	t_r		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	113	-	nS
Turn-Off Fall Time	t_f		-	48	-	nS
Total Gate Charge	Q_g	$V_{DS}=75V, I_D=40A,$ $V_{GS}=10V$	-	138	-	nC
Gate-Source Charge	Q_{gs}		-	46	-	nC
Gate-Drain Charge	Q_{gd}		-	39	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=40A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	100	A
Reverse Recovery Time	t_{rr}	$T_j=25^{\circ}C, I_F=40A, di/dt=100A/\mu s$ (Note3)	-	45		nS
Reverse Recovery Charge	Q_{rr}		-	80		nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

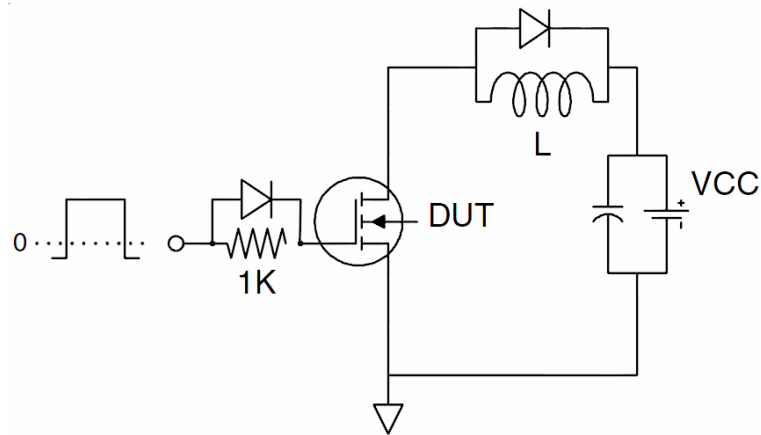
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test circuit

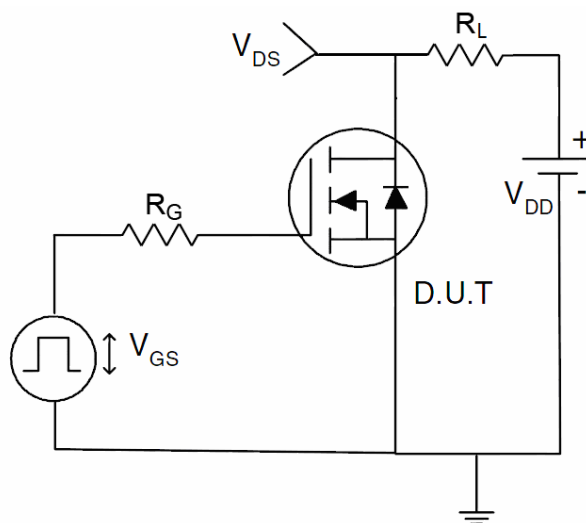
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

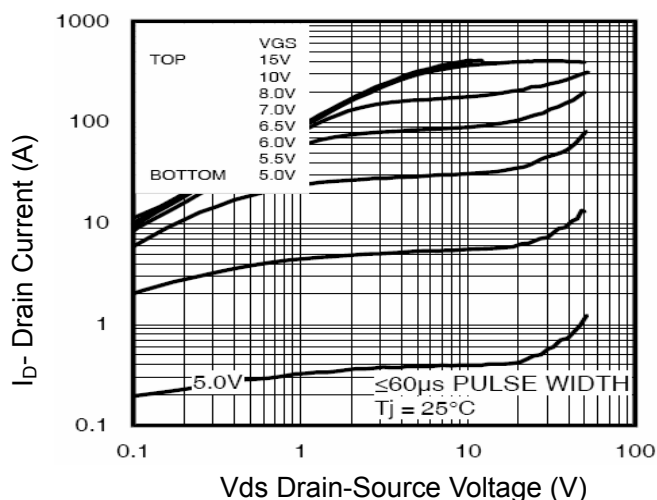


Figure 1 Output Characteristics

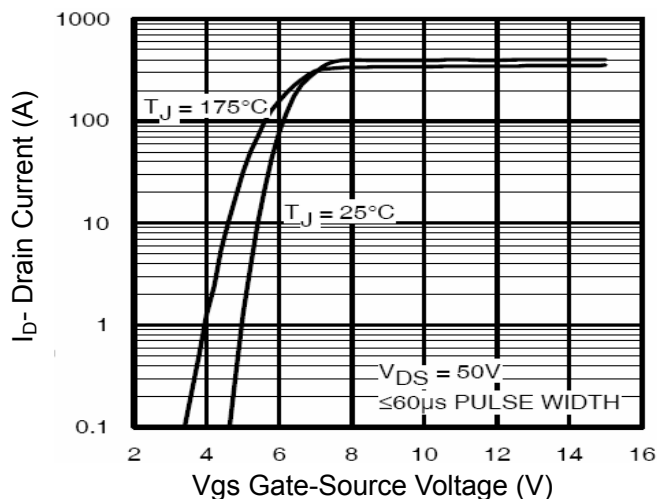


Figure 2 Transfer Characteristics

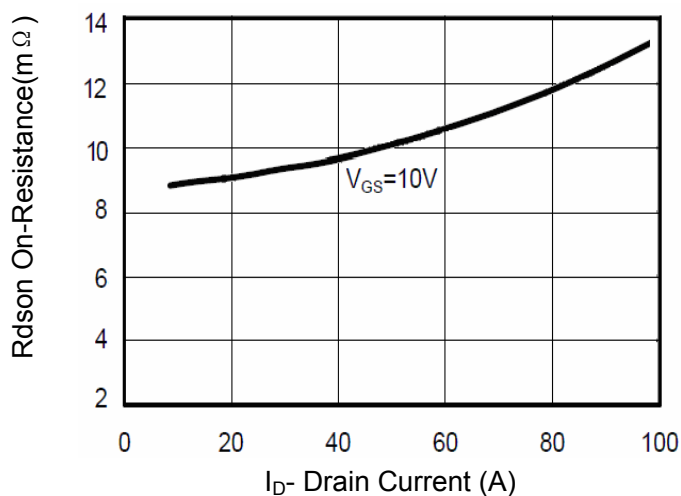


Figure 3 Rdson- Drain Current

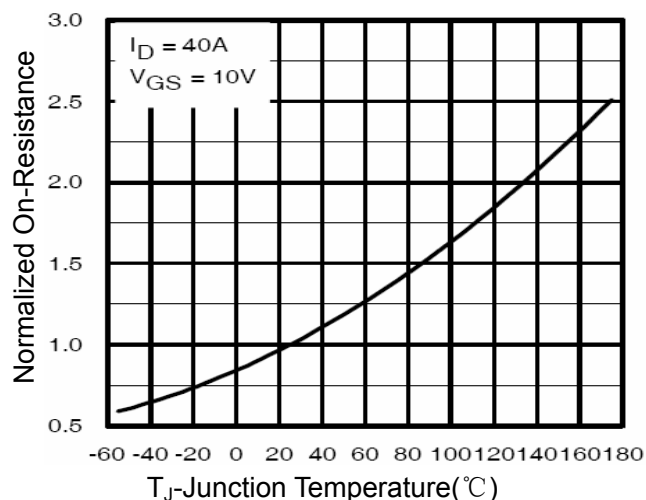


Figure 4 Rdson-Junction Temperature

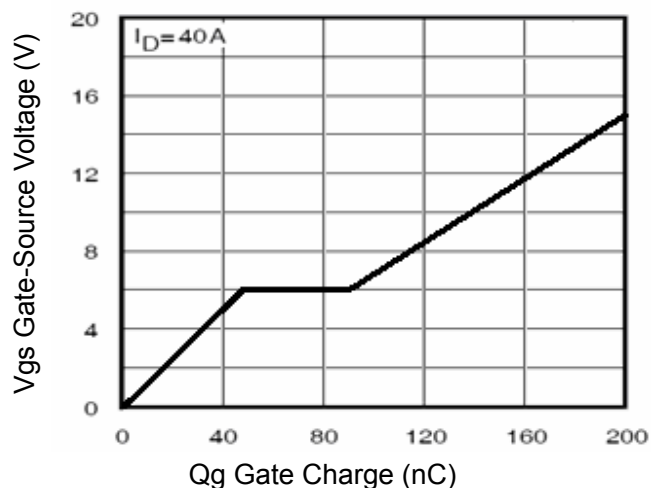


Figure 5 Gate Charge

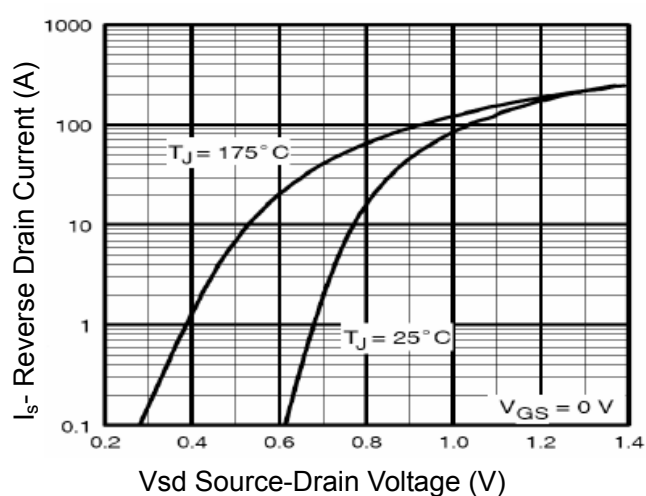


Figure 6 Source- Drain Diode Forward

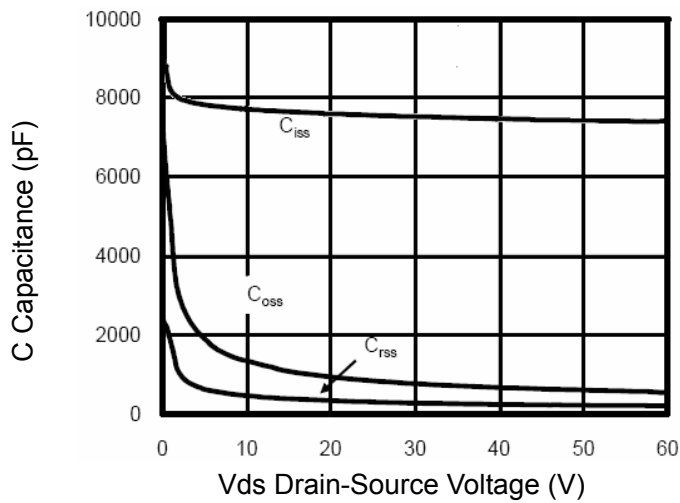


Figure 7 Capacitance vs Vds

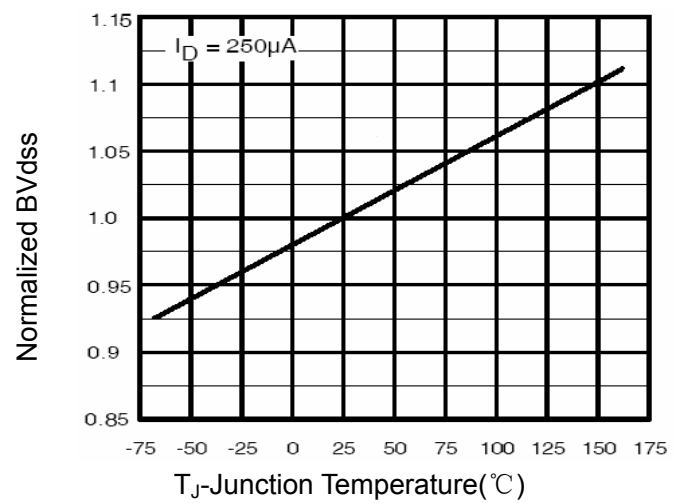


Figure 9 BV_{dss} vs Junction Temperature

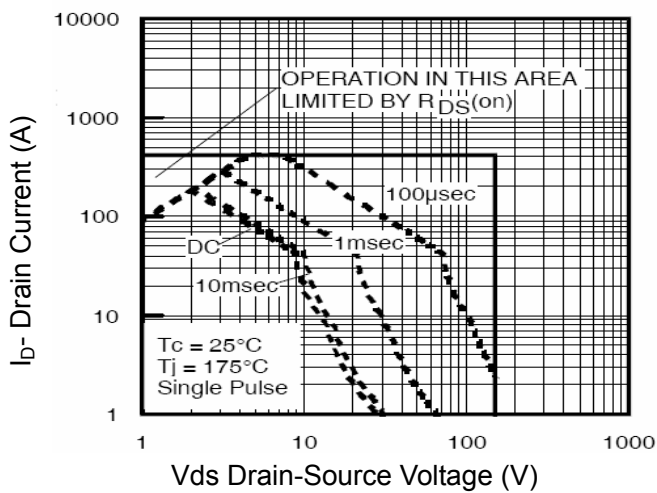


Figure 8 Safe Operation Area

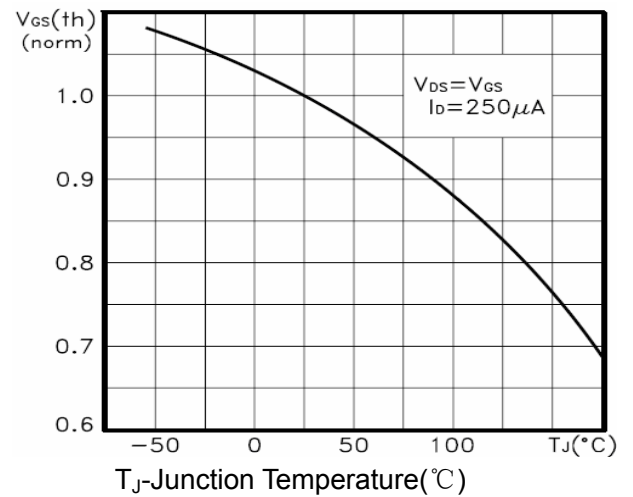


Figure 10 $V_{GS(th)}$ vs Junction Temperature

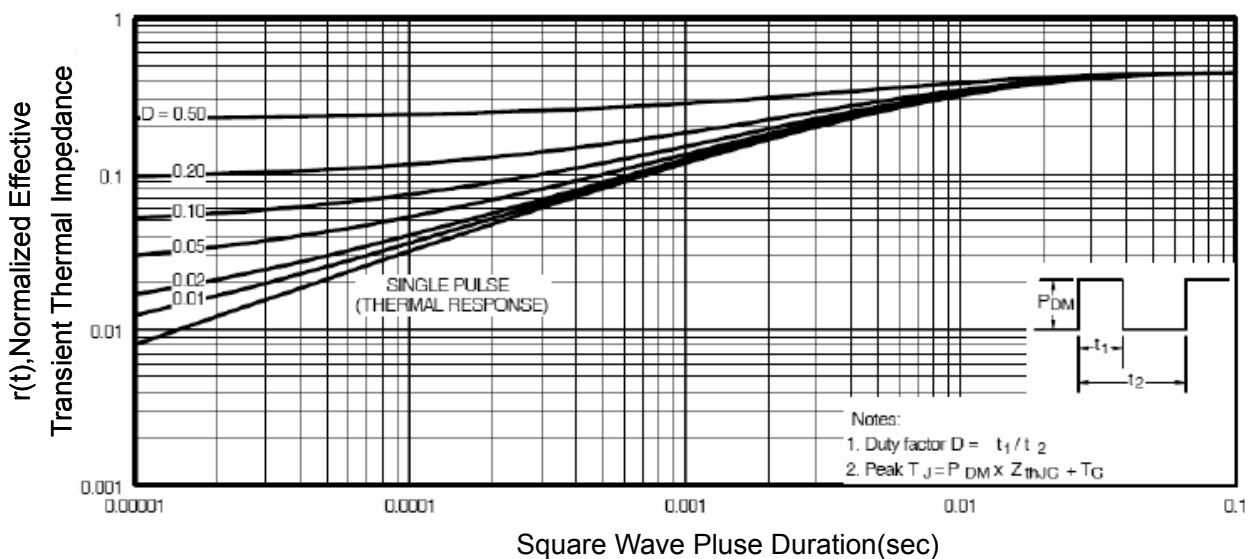
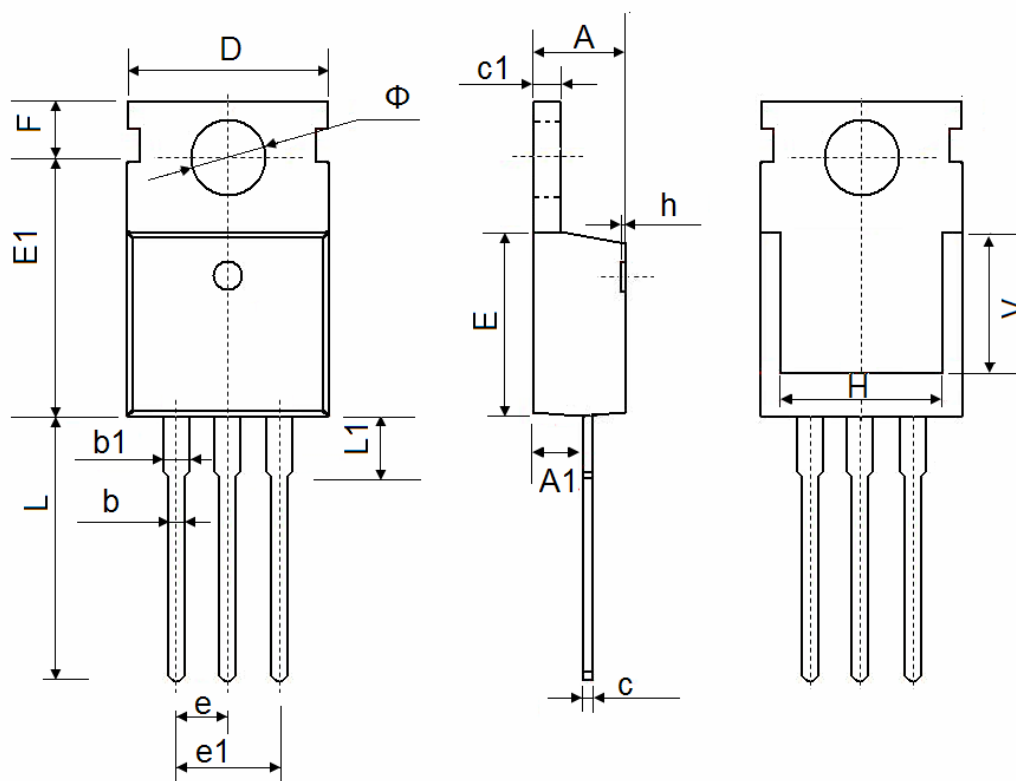


Figure 11 Normalized Maximum Transient Thermal Impedance



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150